

ST1S06xx

Synchronous rectification with inhibit, 1.5 A, 1.5 MHz fixed or adjustable, step-down switching regulator

Features

- Step-down current mode PWM (1.5 MHz) DC-DC converter
- 2% DC output voltage tolerance
- Synchronous rectification
- Inhibit function
- Internal soft start
- Typical efficiency: > 90 %
- 1.5 A output current capability
- Not switching quiescent current: max 1.5 mA over temperature range
- R_{DS(ON)} typ.150 mΩ
- Uses tiny capacitors and inductors
- Operative junction temp. 30 °C to 125 °C
- Available in DFN6D (3x3 mm) exposed pad

Description

The ST1S06xx is a step down DC-DC converter optimized for powering low-voltage digital core in HDD applications and, generally, to replace the high current linear solution when the power dissipation may cause an high heating of the application environment. It provides up to 1.5 A over an input voltage range of 2.7 V to 6 V. An high switching frequency (1.5 MHz) allows the use of tiny surface-mount components: as well as the resistor divider to set the output voltage value, only an inductor and two capacitors are required.

DFN6D (3x3 mm)	

Besides, a low output ripple is guaranteed by the current mode PWM topology and by the use of low ESR SMD ceramic capacitors. The device is thermal protected and current limited to prevent damages due to accidental short circuit. The ST1S06xx is available in DFN6D (3x3 mm) package.

Part numbers	Marking	Order codes	Package
ST1S06	ST1S06	ST1S06PUR	DFN6D (3 x 3 mm)
ST1S06A	ST1S06A	ST1S06APUR	DFN6D (3 x 3 mm)
ST1S06XX12	1S0612	ST1S06PU12R	DFN6D (3 x 3 mm)
ST1S06XX33	1S0633	ST1S06PU33R	DFN6D (3 x 3 mm)

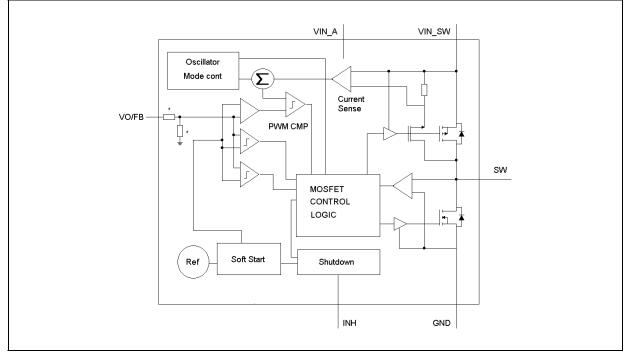
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1 Diagram

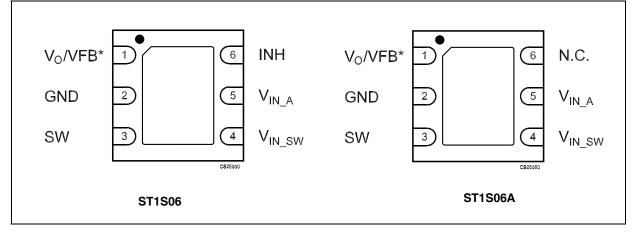






Pin configuration 2





 * Pin 1 is V_{FB} for ADJ version and V_{O} for Fixed version

Table 2.	Pin descriptio	n
Pin n°	Symbol	Note
1	FB/V _O	Feedback voltage / output voltage
2	GND	System ground
3	SW	Switching pin
4	V _{IN_SW}	Power supply for the mosfet switch
5	V _{IN_A}	Power supply for analogic circuit
6	V _{INH}	Inhibit pin to turn off the device
		Exposed pad to be connected to GND

Din description Tabla 2

Value

55 10 Unit °C/W

°C/W

3 Maximum ratings

Symbol	Parameter	Value	Unit
V _{IN_SW}	Positive power supply voltage	-0.3 to 7	V
V _{IN_A}	Positive power supply voltage	-0.3 to 7	V
V _{INH}	Inhibit voltage	-0.3 to V _I + 0.3	V
SWITCH voltage	Max. voltage of output pin	-0.3 to 7	V
V _{FB} /V _O	Feedback voltage	-0.3 to 2.5	V
V _O	Output voltage (for $V_0 > 1.6 V$)	-0.3 to 6	V
TJ	Max junction temperature	-40 to 150	°C
T _{STG}	Storage temperature range	-65 to 150	°C
T _{LEAD}	Lead temperature (soldering) 10 sec	260	°C

Table 3. Absolute maximum ratings

Note: Absolute maximum ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

able 4.	i nermai data	
Symbol	Parameter	
R _{thJA}	Thermal resistance junction-ambient	

Thermal resistance junction-case

Table 4. Thermal data

 $\mathsf{R}_{\mathsf{thJC}}$



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4 Electrical characteristics

 $V_{IN_SW} = V_{IN_A} = V_{INH} = 5 \text{ V}, V_O = 1.2 \text{ V}, C_I = 4.7 \mu\text{F}, C_O = 22 \mu\text{F}, L1 = 3.3 \mu\text{H}, T_J = -30 \text{ °C}$ to 125 °C unless otherwise specified. Typical values are referred to $T_J = 25 \text{ °C}$.

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
FB	Feedback voltage		784	800	816	mV
I _{FB}	V _{FB} pin bias current				600	nA
VI	Minimum input voltage	I _O = 10mA to 1.5A	2.7			V
		V _{INH} > 1.2V			1.5	mA
Ι _Q	Quiescent current	V_{INH} < 0.4V, T_{J} = -30°C to 85°C			1	μA
Ι _Ο	Output current	V _I = 2.7 to 5.5V <i>Note 1</i>	1.5			Α
		Device ON, $V_I = 2.7$ to 5.5V	1.3			
V _{INH}	Inhibit threshold	Device ON, $V_I = 2.7$ to 5V	1.2			V
		Device OFF			0.4	
I _{INH}	Inhibit pin current				2	μA
%V _O /ΔV _I	Reference line regulation	V _I = 2.7V to 5.5V <i>Note 1</i>		0.2	0.3	%V _O / ΔV _I
%V _O /∆I _O	Reference load regulation	I _O = 10mA to 1.5A <i>Note 1</i>		0.2	0.3	%V _O / ΔI _O
PWMf _S	PWM switching frequency	V _{FB} = 0.8V	1.2	1.5	1.8	MHz
D _{MAX}	Maximum duty cycle		80	87		%
R _{DSON} -N	NMOS switch on resistance	I _{SW} = 750 mA		0.12		Ω
R _{DSON} -P	PMOS switch on resistance	I _{SW} = 750 mA		0.15		Ω
I _{SWL}	Switching current limitation	Note 1		2.3		А
		$I_{O} = 10$ mA to 100mA, $V_{O} = 3.3$ V	65			~ %
ν	Efficiency Note 1	$I_0 = 100$ mA to 1.5A, $V_0 = 3.3$ V	85	90		
T _{SHDN}	Thermal shutdown		130	150		°C
T _{HYS}	Thermal shutdown hysteresis			15		°C
%V _O /∆I _O	Load transient response	$I_O = 100mA$ to 750mA, $T_J = 25^{\circ}C t_R = t_F \ge 200ns$, <i>Note 1</i>	-5		+5	%V _O
%V _O /∆I _O	Short circuit removal response	$I_O = 10$ mA to $I_O =$ short, $T_J = 25^{\circ}$ C <i>Note 1</i>	-10		+10	%V _O

 Table 5.
 Electrical characteristics for ST1S06

Note: 1 Guaranteed by design, but not tested in production



 V_{IN_SW} = V_{IN_A} = V_{INH} = 5 V, V_O = 1.2 V, C_I = 4.7 μ F, C_O = 22 μ F, L1 = 3.3 μ H, T_J = -30 °C to 125 °C unless otherwise specified. Typical values are referred to T_J = 25 °C.

Table 6.Electrical characteristics for ST1S06PM12

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
OUT	Output feedback pin		1.176	1.2	1.224	V
Ι _Ο	I _O pin bias current	V _O = 1.5V		15	20	μA
VI	Minimum input voltage	I _O = 10mA to 1.5A	2.7			V
	Quiescent current	V _{INH} > 1.2V			1.5	mA
Ι _Q	Quiescent current	V_{INH} < 0.4V, T_{J} = -30°C to 85°C			1	μΑ
Ι _Ο	Output current	V _I = 2.7 to 5.5V <i>Note 1</i>	1.5			Α
V _{INH}		Device ON, $V_I = 2.7$ to 5.5V	1.3			
	Inhibit threshold	Device ON, $V_I = 2.7$ to 5V	1.2			V
		Device OFF			0.4	
I _{INH}	Inhibit pin current				2	μA
$%V_{O}/\Delta V_{I}$	Reference line regulation	V ₁ = 2.7V to 5.5V <i>Note 1</i>		0.2	0.3	%V _O / ΔV _I
%V _O /∆I _O	Reference load regulation	I _O = 10mA to 1.5A <i>Note 1</i>		0.2	0.3	%V _O / ΔI _O
PWMf _S	PWM switching frequency	V _{FB} = 0.8V	1.2	1.5	1.8	MHz
D _{MAX}	Maximum duty cycle		80	87		%
R _{DSON} -N	NMOS switch on resistance	I _{SW} = 750 mA		0.12		Ω
R _{DSON} -P	PMOS switch on resistance	I _{SW} = 750 mA		0.15		Ω
I _{SWL}	Switching current limitation	Note 1		2.3		Α
		$I_{\rm O}$ = 10mA to 100mA, $V_{\rm O}$ = 1.2V	60			%
ν	Efficiency Note 1	I_{O} = 100mA to 1.5A, V_{O} = 1.2V	80	85		
T _{SHDN}	Thermal shutdown		130	150		°C
T _{HYS}	Thermal shutdown hysteresis			15		°C
$V_0/\Delta I_0$	Load transient response	$I_{O} = 100mA \text{ to } 750mA, T_{J} = 25^{\circ}C t_{R} = t_{F} \ge 200ns, Note 1$	-5		+5	%V _O
$V_0/\Delta I_0$	Short circuit removal response	$I_O = 10$ mA to $I_O =$ short, $T_J = 25^{\circ}$ C <i>Note 1</i>	-10		+10	%V _O

Note: 1 Guaranteed by design, but not tested in production

 V_{IN_SW} = V_{IN_A} = V_{INH} = 5 V, V_O = 3.3 V, C_I = 4.7 μ F, C_O = 22 μ F, L1 = 3.3 μ H, T_J = -30 °C to 125 °C unless otherwise specified. Typical values are referred to T_J = 25 °C.

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
OUT	Output feedback pin		3.23	3.3	3.37	V
Ι _Ο	I _O pin bias current	V _O = 3.5V		15	20	μA
VI	Minimum input voltage	I _O = 10mA to 1.5A	4.2			V
	Outercent current	V _{INH} > 1.2V			1.5	mA
Ι _Q	Quiescent current	$V_{\rm INH}$ < 0.4V, $T_{\rm J}$ = -30°C to 85°C			1	μA
Ι _Ο	Output current	V _I = 4.2 to 5.5V <i>Note 1</i>	1.5			Α
		Device ON, $V_1 = 4.2$ to 5.5V	1.3			
V _{INH}	Inhibit threshold	Device ON, $V_I = 4.2$ to 5V	1.2			v
		Device OFF			0.4	
I _{INH}	Inhibit pin current				2	μA
$%V_{O}/\Delta V_{I}$	Reference line regulation	V _I = 4.2V to 5.5V <i>Note 1</i>		0.2	0.3	%V _O / ΔV _I
$V_0/\Delta I_0$	Reference load regulation	I _O = 10mA to 1.5A <i>Note 1</i>		0.2	0.3	%V _O / ΔI _O
PWMf _S	PWM switching frequency	V _{FB} = 0.8V	1.2	1.5	1.8	MHz
D _{MAX}	Maximum duty cycle		80	87		%
R _{DSON} -N	NMOS switch on resistance	I _{SW} = 750 mA		0.12		Ω
R _{DSON} -P	PMOS switch on resistance	I _{SW} = 750 mA		0.15		Ω
I _{SWL}	Switching current limitation	Note 1		2.3		Α
	Efficiency Note 1	$I_{O} = 10$ mA to 100mA, $V_{O} = 3.3$ V	65			%
ν		$I_{O} = 100$ mA to 1.5A, $V_{O} = 3.3$ V	85	90		
T _{SHDN}	Thermal shutdown		130	150		°C
T _{HYS}	Thermal shutdown hysteresis			15	1	°C
$V_0/\Delta I_0$	Load transient response	$I_{O} = 100mA \text{ to } 750mA, T_{J} = 25^{\circ}C t_{R} = t_{F} \ge 200ns, Note 1$	-5		+5	%V _O
$V_0/\Delta I_0$	Short circuit removal response	$I_O = 10mA$ to $I_O = short$, $T_J = 25^{\circ}C$ <i>Note 1</i>	-10		+10	%V _O

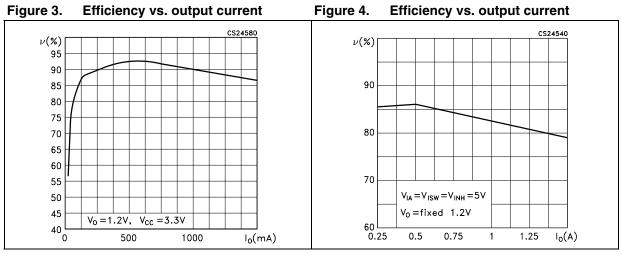
 Table 7.
 Electrical characteristics for ST1S06PM33

Note: 1 Guaranteed by design, but not tested in production



5 Typical performance characteristics

 $V_{IN_SW} = V_{IN_A} = V_{INH} = 5$ V, $C_I = 4.7 \ \mu$ F, $C_O = 22 \ \mu$ F, L1 = 3.3 μ H, unless otherwise specified. Typical values are referred to 25 °C.







Efficiency vs. inductor

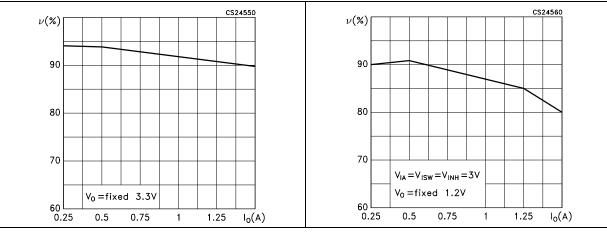
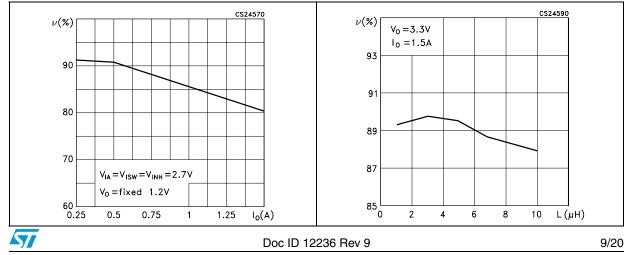


Figure 8.





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 $V_0(V)$

Figure 10. Input voltage vs. output voltage

2.5

Figure 12. Quiescent current vs. temperature

3

 $R_{LOAD} = 0.8 \Omega$

 $V_{I}(V)$

1.4

1.2

1.0

0.8 0.6

0.4

0.2

0 × 2

Figure 9.	Voltage	feedback vs.	temperature
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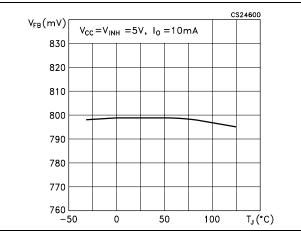
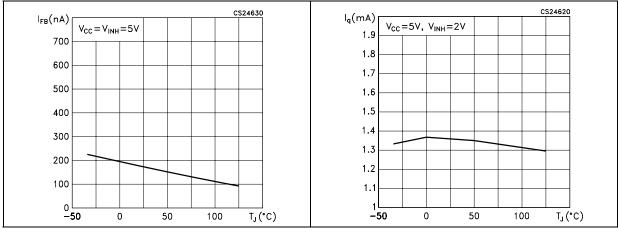
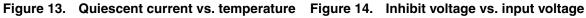
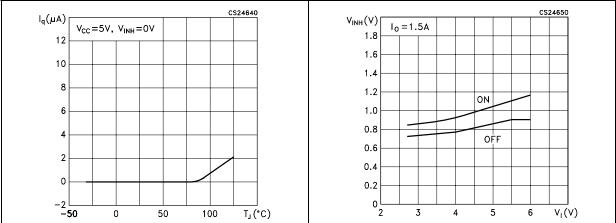


Figure 11. Feedback pin bias current vs. temperature









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Load regulation vs. temperature

Figure 15.	Inhibit voltage vs. temperature	ł
i igaio ioi	initial voltage ver temperature	

Figure 16. Inhibit voltage vs. temperature

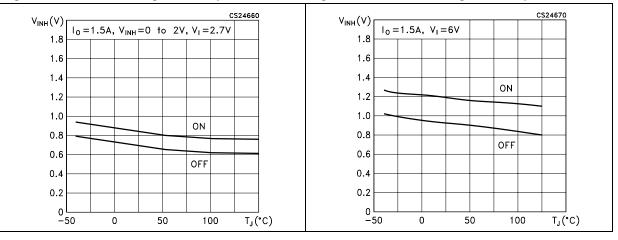


Figure 18.



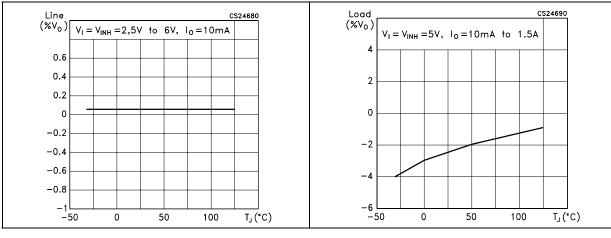


Figure 19. PWM switching frequency vs. temperature

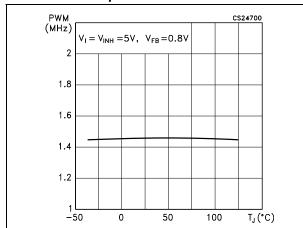
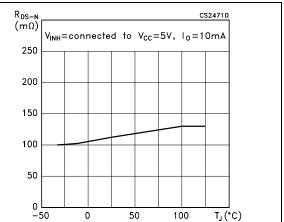


Figure 20. NMOS switch on resistance vs. temperature



R_{DS-P} (mΩ)

250

200

150

100

50

0

-50

 V_{INH} = connected to V_{CC} = 5V, I_0 = 10mA

50

100

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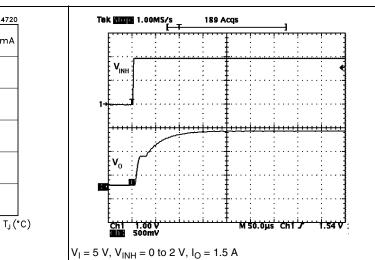
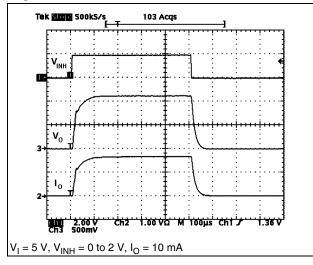


Figure 23. Inhibit transient

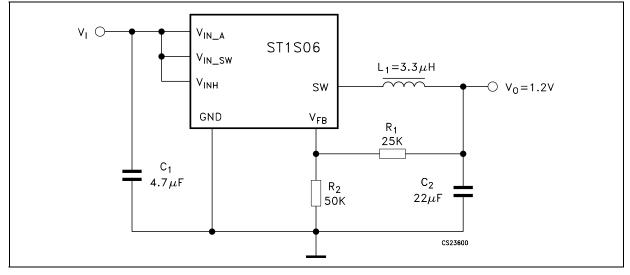
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ST1S06xx

6 Typical application

Figure 24. Application circuit





7 Application notes

The ST1S06xx is an adjustable current mode PWM step-down DC-DC converter with internal 1.5 A power switch, packaged in a 6-lead DFN 3x3.

It's a complete 1.5 A switching regulator with its internal compensation eliminating additional component.

The constant frequency, current mode, PWM architecture and stable operation with ceramic capacitors results in low, predictable output ripple. However, in order to maximize the power conversion efficiency with light load, the regulator reduces automatically the switching frequency when the output load becomes less than 250 mA typically.

To clamp the error amplifier reference voltage a soft start control block generating a voltage ramp, has been implemented. Besides an on-chip power on reset of $50 = 100 \,\mu\text{s}$ ensure the proper operation when switching on the power supply. Other circuits fitted to the device protection are the thermal shut down block which turn off the regulator when the junction temperature exceeds 150 °C typically and the cycle-by-cycle current limiting that provides protection against shorted outputs.

Being the ST1S06xx an adjustable regulator, the output voltage is determined by an external resistor divider. The desired value is given by the following equation:

 $V_0 = V_{FB} [1 + R_1 / R_2]$

To make the device working, only few component are required: an inductor and two capacitors and the resistor divider. The chosen inductor must be able to not saturate at the peak current level. Besides, its value can be selected keeping in account that a large inductor value increases the efficiency at low output current and reduces output voltage ripple, while a smaller inductor can be chosen when it is important to reduce the package size and the total cost of the application. Finally, the ST1S06xx has been designed to work properly with X5R or X7R SMD ceramic capacitors both at the input and at the output. this kind of capacitors, thanks to their very low series resistance (ESR), minimize the output voltage ripple. Other low ESR capacitors can be used according to the need of the application without invalidate the right functioning of the device.



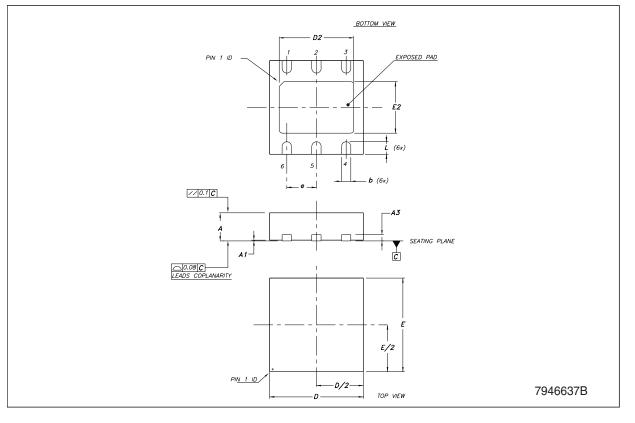
8 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.



DFN6D (3x3 mm) mechanical data

Dim.	mm.			inch.		
	Min.	Тур.	Max.	Min.	Тур.	Max.
А	0.80		1.00	0.031		0.039
A1	0	0.02	0.05	0	0.001	0.002
A3		0.20			0.008	
b	0.23		0.45	0.009		0.018
D	2.90	3.00	3.10	0.114	0.118	0.122
D2	2.23		2.50	0.088		0.098
E	2.90	3.00	3.10	0.114	0.118	0.122
E2	1.50		1.75	0.059		0.069
е		0.95			0.037	
L	0.30	0.40	0.50	0.012	0.016	0.020

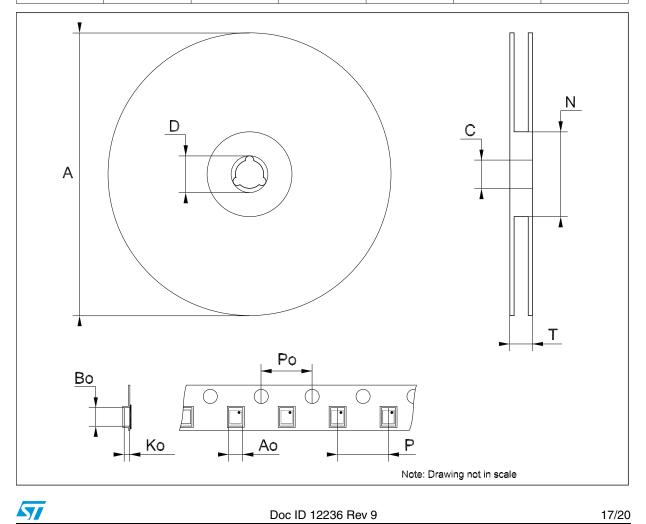


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Tape and reel QFNxx/DFNxx (3x3 mm) mechanical data

Dim.	mm.			inch.		
	Min.	Тур.	Max.	Min.	Тур.	Max.
А			330			12.992
С	12.8		13.2	0.504		0.519
D	20.2			0.795		
Ν	60			2.362		
Т			18.4			0.724
Ao		3.3			0.130	
Во		3.3			0.130	
Ko		1.1			0.043	
Po		4			0.157	
Р		8			0.315	



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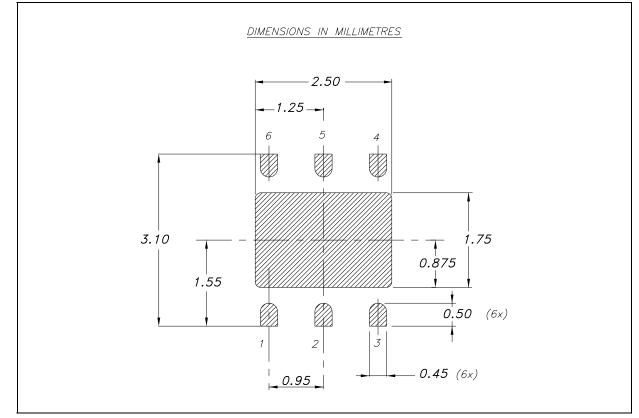


Figure 25. DFN6 (3x3 mm) footprint recommended data



9 Revision history

Date	Revision	Changes	
08-May-2006	1	Initial release.	
06-Jun-2006	2	Table 3 updated.	
16-Oct-2006	3	Add new mechanical data DFN6D.	
09-Nov-2006	4	Mechanical data information for DFN6 update.	
03-Apr-2007	5	Tape and reel updated.	
12-Mar-2008	6	Added: Table 1 on page 1.	
15-Apr-2008	7	Modified: <i>Figure 6 on page 9</i> .	
10-Apr-2009	8	Modified: Table 3 on page 5.	
06-May-2009	9	Added: marking <i>Table 1 on page 1</i> .	

Table 8.Document revision history



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